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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8548vtaujc

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

- VRRP and HSRP support for seamless router fail-over
- Up to 16 exact-match MAC addresses supported
- Broadcast address (accept/reject)
- Hash table match on up to 512 multicast addresses
- Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status
- Ability to force allocation of header information and buffer descriptors into L2 cache
- OCeaN switch fabric
 - Full crossbar packet switch
 - Reorders packets from a source based on priorities
 - Reorders packets to bypass blocked packets
 - Implements starvation avoidance algorithms
 - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
 - Four-channel controller
 - All channels accessible by both the local and remote masters
 - Extended DMA functions (advanced chaining and striding capability)
 - Support for scatter and gather transfers
 - Misaligned transfer capability
 - Interrupt on completed segment, link, list, and error
 - Supports transfers to or from any local memory or I/O port
 - Selectable hardware-enforced coherency (snoop/no snoop)
 - Ability to start and flow control each DMA channel from external 3-pin interface
 - Ability to launch DMA from single write transaction
- Two PCI/PCI-X controllers
 - PCI 2.2 and PCI-X 1.0 compatible
 - One 32-/64-bit PCI/PCI-X port with support for speeds of up to 133 MHz (maximum PCI-X frequency in synchronous mode is 110 MHz)
 - One 32-bit PCI port with support for speeds from 16 to 66 MHz (available when the other port is in 32-bit mode)
 - Host and agent mode support
 - 64-bit dual address cycle (DAC) support
 - PCI-X supports multiple split transactions
 - Supports PCI-to-memory and memory-to-PCI streaming

Overview

- Memory prefetching of PCI read accesses
- Supports posting of processor-to-PCI and PCI-to-memory writes
- PCI 3.3-V compatible
- Selectable hardware-enforced coherency
- Serial RapidIO[™] interface unit
 - Supports RapidIO[™] Interconnect Specification, Revision 1.2
 - Both $1 \times$ and $4 \times$ LP-serial link interfaces
 - Long- and short-haul electricals with selectable pre-compensation
 - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
 - Auto detection of 1- and 4-mode operation during port initialization
 - Link initialization and synchronization
 - Large and small size transport information field support selectable at initialization time
 - 34-bit addressing
 - Up to 256 bytes data payload
 - All transaction flows and priorities
 - Atomic set/clr/inc/dec for read-modify-write operations
 - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
 - Receiver-controlled flow control
 - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
 - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
 - Hardware recovery only
 - Register support is not required for software-mediated error recovery.
 - Accept-all mode of operation for fail-over support
 - Support for RapidIO error injection
 - Internal LP-serial and application interface-level loopback modes
 - Memory and PHY BIST for at-speed production test
- RapidIO-compatible message unit
 - 4 Kbytes of payload per message
 - Up to sixteen 256-byte segments per message
 - Two inbound data message structures within the inbox
 - Capable of receiving three letters at any mailbox
 - Two outbound data message structures within the outbox
 - Capable of sending three letters simultaneously
 - Single segment multicast to up to 32 devIDs
 - Chaining and direct modes in the outbox

Characteristic	Symbol	Max Value	Unit	Notes	
Storage temperature range	T _{STG}	-55 to 150	°C	_	

Table 1. Absolute Maximum Ratings ¹ (continued)

Notes:

- 1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- 2. The -0.3 to 2.75 V range is for DDR and -0.3 to 1.98 V range is for DDR2.
- 3. The 3.63 V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75 V maximum applies. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
- 4. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply volta	age	V _{DD}	1.1 V ± 55 mV	V	—
PLL supply voltage	ge	AV _{DD}	1.1 V ± 55 mV	V	1
Core power supp	ly for SerDes transceivers	SV _{DD}	1.1 V ± 55 mV	V	—
Pad power suppl	y for SerDes transceivers	XV _{DD}	1.1 V ± 55 mV	V	—
DDR and DDR2	DRAM I/O voltage	GV _{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	
Three-speed Ethernet I/O voltage		LV _{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	4
		TV _{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	_	4
	RT, system control and power management, I ² C, nagement, and JTAG I/O voltage	OV _{DD}	3.3 V ± 165 mV	V	3
Local bus I/O vol	tage	BV _{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	
Input voltage	DDR and DDR2 DRAM signals	MV _{IN}	GND to GV _{DD}	V	2
	DDR and DDR2 DRAM reference	MV _{REF}	GND to GV _{DD} /2	V	2
Three-speed Ethernet signals		LV _{IN} TV _{IN}	GND to LV _{DD} GND to TV _{DD}	V	4
	Local bus signals	BV _{IN}	GND to BV _{DD}	V	—
	PCI, DUART, SYSCLK, system control and power management, I ² C, Ethernet MII management, and JTAG signals	OV _{IN}	GND to OV _{DD}	V	3

Table 2. Recommended Operating Conditions

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 3.3 \text{ V DC}$.

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = BV_{DD})$	I _{IN}	_	±5	μA
High-level output voltage ($BV_{DD} = min, I_{OH} = -2 mA$)	V _{OH}	2.4	—	V
Low-level output voltage ($BV_{DD} = min$, $I_{OL} = 2 mA$)	V _{OL}	—	0.4	V

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Note:

1. Note that the symbol V_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 2.5 \text{ V DC}$.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

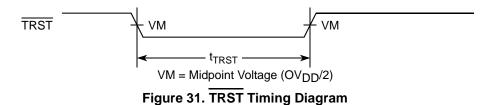
Parameter	Symbol	Min	Max	Unit
High-level input voltage	V _{IH}	1.70	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.7	V
Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = BV_{DD})$	I _{IH}	_	10	μA
	I		-15	
High-level output voltage ($BV_{DD} = min, I_{OH} = -1 mA$)	V _{OH}	2.0	—	V
Low-level output voltage ($BV_{DD} = min$, $I_{OL} = 1 mA$)	V _{OL}	_	0.4	V

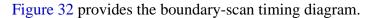
Note:

1. Note that the symbol V_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

JTAG

Figure 31 provides the $\overline{\text{TRST}}$ timing diagram.





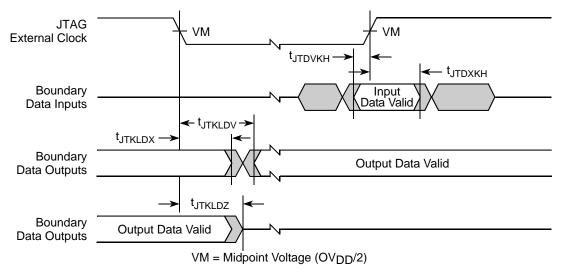


Figure 32. Boundary-Scan Timing Diagram

PCI/PCI-X

Figure 36 shows the PCI/PCI-X input AC timing conditions.

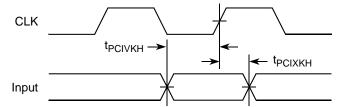


Figure 36. PCI/PCI-X Input AC Timing Measurement Conditions

Figure 37 shows the PCI/PCI-X output AC timing conditions.

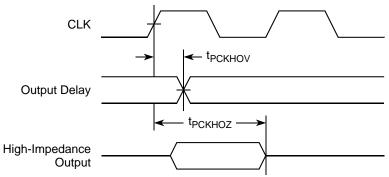




Table 53 provides the PCI-X AC timing specifications at 66 MHz.

Table 53. PCI-X AC Timing	Specifications at 66 MHz
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Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	^t PCKHOV	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t _{РСКНОХ}	0.7	—	ns	1, 10
SYSCLK to output high impedance	t _{PCKHOZ}	—	7	ns	1, 4, 8, 11
Input setup time to SYSCLK	t _{PCIVKH}	1.7	—	ns	3, 5
Input hold time from SYSCLK	t _{PCIXKH}	0.5	—	ns	10
REQ64 to HRESET setup time	t _{PCRVRH}	10	—	clocks	11
HRESET to REQ64 hold time	t _{PCRHRX}	0	50	ns	11
HRESET high to first FRAME assertion	t _{PCRHFV}	10	—	clocks	9, 11
PCI-X initialization pattern to HRESET setup time	^t PCIVRH	10	—	clocks	11

High-Speed Serial Interfaces (HSSI)

- The input amplitude of the differential clock must be between 400 and 1600 mV differential peak-peak (or between 200 and 800 mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800 mV and greater than 200 mV. This requirement is the same for both external DC- or AC-coupled connection.
- For external DC-coupled connection, as described in Section 16.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 and 400 mV. Figure 40 shows the SerDes reference clock input requirement for DC-coupled connection scheme.
- For external AC-coupled connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SGND_SRDSn. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SGND_SRDSn). Figure 41 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- Single-ended mode
 - The reference clock can also be single-ended. The SD_REF_CLK input amplitude (single-ended swing) must be between 400 and 800 mV peak-to-peak (from V_{min} to V_{max}) with SD_REF_CLK either left unconnected or tied to ground.
 - The SD_REF_CLK input average voltage must be between 200 and 400 mV. Figure 42 shows the SerDes reference clock input requirement for single-ended signaling mode.
 - To meet the input amplitude requirement, the reference clock inputs might need to be DC- or AC-coupled externally. For the best noise performance, the reference of the clock could be DCor AC-coupled into the unused phase (SD_REF_CLK) through the same source impedance as the clock input (SD_REF_CLK) in use.

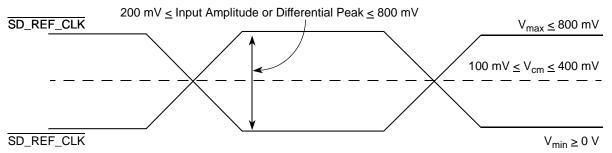


Figure 40. Differential Reference Clock Input DC Requirements (External DC-Coupled)

High-Speed Serial Interfaces (HSSI)

Figure 43 shows the SerDes reference clock connection reference circuits for HCSL type clock driver. It assumes that the DC levels of the clock driver chip is compatible with SerDes reference clock input's DC requirement.

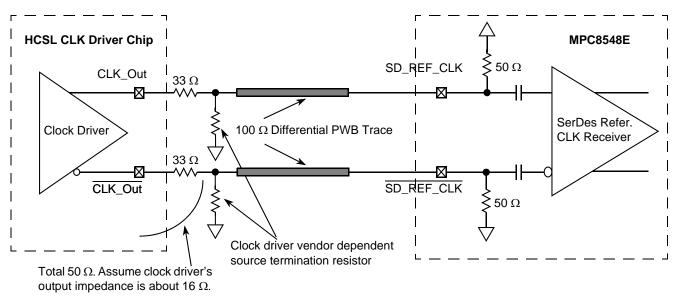




Figure 44 shows the SerDes reference clock connection reference circuits for LVDS type clock driver. Since LVDS clock driver's common mode voltage is higher than the SerDes reference clock input's allowed range (100–400 mV), AC-coupled connection scheme must be used. It assumes the LVDS output driver features 50- Ω termination resistor. It also assumes that the LVDS transmitter establishes its own common mode level without relying on the receiver or other external component.

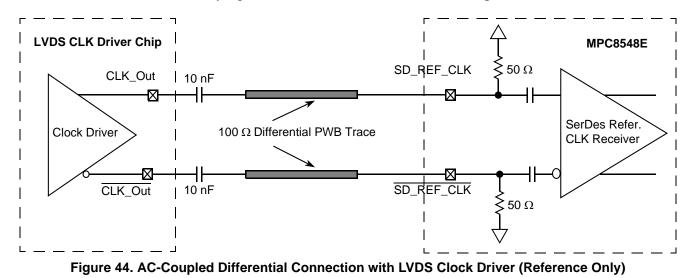


Figure 45 shows the SerDes reference clock connection reference circuits for LVPECL type clock driver. Since LVPECL driver's DC levels (both common mode voltages and output swing) are incompatible with the SerDes reference clock input's DC requirement, AC-coupling must be used. Figure 45 assumes that the LVPECL clock driver's output impedance is 50 Ω . R1 is used to DC-bias the LVPECL outputs prior

to AC-coupling. Its value could be ranged from 140 to 240 Ω depending on the clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50- Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the SerDes reference clock's differential input amplitude requirement (between 200 and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω . Consult a clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.

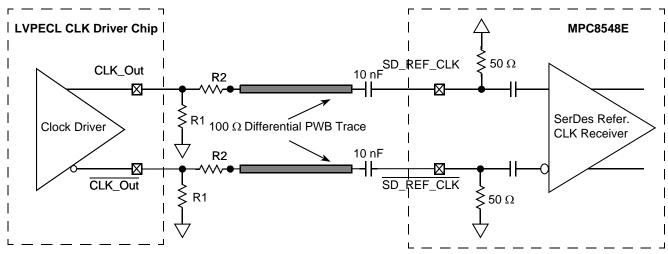


Figure 45. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

Figure 46 shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with the SerDes reference clock input's DC requirement.

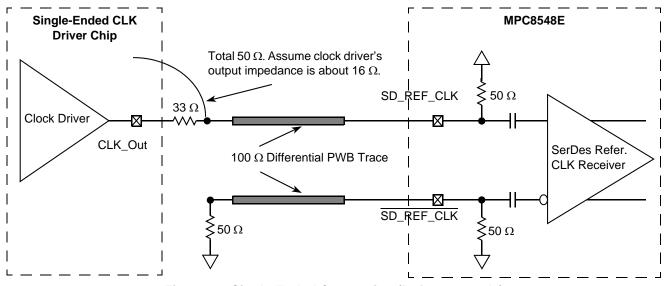


Figure 46. Single-Ended Connection (Reference Only)

PCI Express

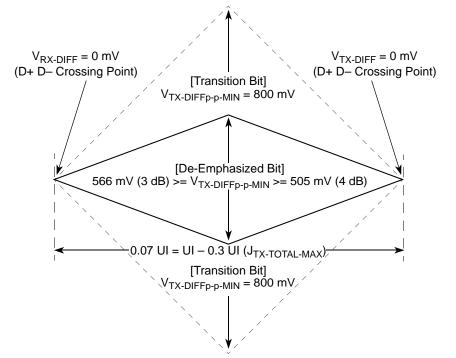


Figure 48. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

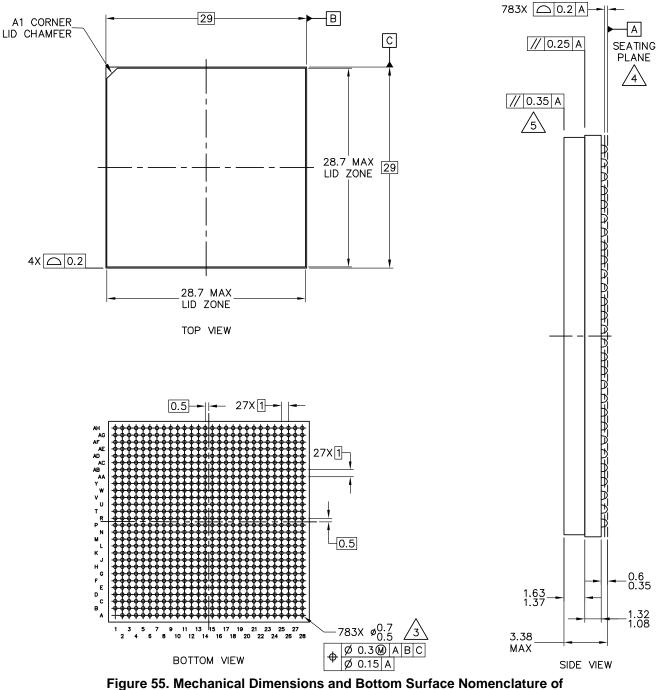
Table 57 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps \pm 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
V _{RX-DIFFp-p}	Differential peak-to-peak input voltage	0.175	—	1.200	V	$V_{RX-DIFFp-p} = 2 \times V_{RX-D+} - V_{RX-D-} $. See Note 2.
T _{RX-EYE}	Minimum receiver eye width	0.4	_	_	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.
T _{RX-EYE-MEDIAN-to-} MAX-JITTER	Maximum time between the jitter median and maximum deviation from the median	—		0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.

Table 57. Differential Receiver (RX) Input Specifications

19.2 Mechanical Dimensions of the HiCTE FC-CBGA and FC-PBGA with Full Lid

The following figures show the mechanical dimensions and bottom surface nomenclature for the MPC8548E HiCTE FC-CBGA and FC-PBGA packages.



the HiCTE FC-CBGA and FC-PBGA with Full Lid

Notes:

- 1. All dimensions are in millimeters.
- 2. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 3. Maximum solder ball diameter measured parallel to datum A.
- 4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
- 5. Parallelism measurement shall exclude any effect of mark on top surface of package.
- 6. All dimensions are symmetric across the package center lines unless dimensioned otherwise.

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_REQ[4:1]	AH2, AG4, AG3, AH4	I	OV _{DD}	_
				_
				—
				—
				—
PCI1_REQ0	AH3	I/O	OV _{DD}	—
PCI1_CLK	AH26	I	OV _{DD}	39
PCI1_DEVSEL	AH11	I/O	OV _{DD}	2
PCI1_FRAME	AE11	I/O	OV _{DD}	2
PCI1_IDSEL	AG9	I	OV _{DD}	—
PCI1_REQ64/PCI2_FRAME	AF14	I/O	OV _{DD}	2, 5, 10
PCI1_ACK64/PCI2_DEVSEL	V15	I/O	OV _{DD}	2
PCI2_CLK	AE28	I	OV _{DD}	39
PCI2_IRDY	AD26	I/O	OV _{DD}	2
PCI2_PERR	AD25	I/O	OV _{DD}	2
PCI2_GNT[4:1]	AE26, AG24, AF25, AE25	0	OV _{DD}	5, 9, 35
PCI2_GNT0	AG25	I/O	OV _{DD}	—
PCI2_SERR	AD24	I/O	OV _{DD}	2, 4
PCI2_STOP	AF24	I/O	OV _{DD}	2
PCI2_TRDY	AD27	I/O	OV _{DD}	2
PCI2_REQ[4:1]	AD28, AE27, W17, AF26	I	OV _{DD}	—
PCI2_REQ0	AH25	I/O	OV _{DD}	—
	DDR SDRAM Memory Interface		1	-
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	0	GV _{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	0	GV _{DD}	—
MBA[0:2]	F7, J7, M11	0	GV _{DD}	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	DFT	I I		
L1_TSTCLK	AC25	I	OV _{DD}	25
L2_TSTCLK	AE22	I	OV _{DD}	25
LSSD_MODE	AH20	I	OV_{DD}	25
TEST_SEL	AH14	I	OV_{DD}	25
	Thermal Management			•
THERM0	AG1	—	_	14
THERM1	AH1	—	_	14
	Power Management			•
ASLEEP	AH18	0	OV _{DD}	9, 19, 29
	Power and Ground Signals	I I		
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	_	_	
OV _{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV _{DD}	_
LV _{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV _{DD}	_
TV _{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV _{DD}	—
GV _{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV _{DD}	—

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV _{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13		GV _{DD}	_
BV _{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV _{DD}	-
V _{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V _{DD}	-
SV _{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV _{DD}	-
XV _{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV _{DD}	-
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	_	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	_	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	_	26
AVDD_PLAT	AH19	Powerfor CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	_	26
SENSEVDD	M14	0	V _{DD}	13
SENSEVSS	M16	—	—	13
	Analog Signals			
MVREF	A18	I Reference voltage signal for DDR	MVREF	

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_TRDY	AG11	I/O	OV _{DD}	2
PCI1_REQ[4:1]	AH2, AG4, AG3, AH4	I	OV _{DD}	
PCI1_REQ0	AH3	I/O	OV _{DD}	—
PCI1_CLK	AH26	I	OV _{DD}	39
PCI1_DEVSEL	AH11	I/O	OV _{DD}	2
PCI1_FRAME	AE11	I/O	OV _{DD}	2
PCI1_IDSEL	AG9	I	OV _{DD}	_
cfg_pci1_width	AF14	I/O	OV _{DD}	112
Reserved	V15	—	_	110
Reserved	AE28	—	—	2
Reserved	AD26	—	_	110
Reserved	AD25	—	_	110
Reserved	AE26	—	—	110
cfg_pci1_clk	AG24	I	OV _{DD}	5
Reserved	AF25	—	_	101
Reserved	AE25	_	—	110
Reserved	AG25	—	_	110
Reserved	AD24	—	_	110
Reserved	AF24	—	_	110
Reserved	AD27	—	_	110
Reserved	AD28, AE27, W17, AF26	—	_	110
Reserved	AH25	—	_	110
	DDR SDRAM Memory Interface			
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV _{DD}	_
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV _{DD}	
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	0	GV_DD	
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV _{DD}	
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV _{DD}	_
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	0	GV _{DD}	_
MBA[0:2]	F7, J7, M11	0	GV _{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes	
MWE	E7	0	GV _{DD}		
MCAS	H7	0	GV _{DD}	—	
MRAS	L8	0	GV _{DD}	—	
MCKE[0:3]	F10, C10, J11, H11	0	GV _{DD}	11	
MCS[0:3]	K8, J8, G8, F8	0	GV _{DD}	- T	
MCK[0:5]	H9, B15, G2, M9, A14, F1	0	GV_DD	—	
MCK[0:5]	J9, A15, G1, L9, B14, F2	0	GV _{DD}	—	
MODT[0:3]	E6, K6, L7, M7	0	GV_DD	—	
MDIC[0:1]	A19, B19	I/O	GV_DD	36	
	Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV _{DD}	_	
LDP[0:3]	K21, C28, B26, B22	I/O	BV _{DD}	—	
LA[27]	H21	0	BV _{DD}	5, 9	
LA[28:31]	H20, A27, D26, A28	0	BV _{DD}	5, 7, 9	
LCS[0:4]	J25, C20, J24, G26, A26	0	BV _{DD}	—	
LCS5/DMA_DREQ2	D23	I/O	BV _{DD}	1	
LCS6/DMA_DACK2	G20	0	BV _{DD}	1	
LCS7/DMA_DDONE2	E21	0	BV _{DD}	1	
LWE0/LBS0/LSDDQM[0]	G25	0	BV _{DD}	5, 9	
LWE1/LBS1/LSDDQM[1]	C23	0	BV _{DD}	5, 9	
LWE2/LBS2/LSDDQM[2]	J21	0	BV _{DD}	5, 9	
LWE3/LBS3/LSDDQM[3]	A24	0	BV _{DD}	5, 9	
LALE	H24	0	BV _{DD}	5, 8, 9	
LBCTL	G27	0	BV _{DD}	5, 8, 9	
LGPL0/LSDA10	F23	0	BV _{DD}	5, 9	
LGPL1/LSDWE	G22	0	BV _{DD}	5, 9	
LGPL2/LOE/LSDRAS	B27	0	BV _{DD}	5, 8, 9	
LGPL3/LSDCAS	F24	0	BV _{DD}	5, 9	
LGPL4/LGTA/LUPWAIT/LPBSE	H23	I/O	BV _{DD}	—	
LGPL5	E26	0	BV _{DD}	5, 9	
LCKE	E24	0	BV _{DD}	—	
LCLK[0:2]	E23, D24, H22	0	BV _{DD}	—	

Signal	Package Pin Number	Pin Type	Power Supply	Notes
IIC1_SDA	AG21	I/O	OV _{DD}	4, 27
IIC2_SCL	AG15	I/O	OV _{DD}	4, 27
IIC2_SDA	AG14	I/O	OV _{DD}	4, 27
	SerDes	1		
SD_RX[0:7]	M28, N26, P28, R26, W26, Y28, AA26, AB28	Ι	XV _{DD}	—
SD_RX[0:7]	M27, N25, P27, R25, W25, Y27, AA25, AB27	Ι	XV _{DD}	_
SD_TX[0:7]	M22, N20, P22, R20, U20, V22, W20, Y22	0	XV _{DD}	—
SD_TX[0:7]	M23, N21, P23, R21, U21, V23, W21, Y23	0	XV _{DD}	_
SD_PLL_TPD	U28	0	XV _{DD}	24
SD_REF_CLK	T28	Ι	XV _{DD}	—
SD_REF_CLK	T27	Ι	XV _{DD}	_
Reserved	AC1, AC3	—	_	2
Reserved	M26, V28	—	_	32
Reserved	M25, V27	_	_	34
Reserved	M20, M21, T22, T23	—	_	38
	General-Purpose Output			•
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	0	BV_DD	—
	System Control			•
HRESET	AG17	Ι	OV _{DD}	—
HRESET_REQ	AG16	0	OV_DD	29
SRESET	AG20	I	OV _{DD}	—
CKSTP_IN	AA9	Ι	OV_{DD}	—
CKSTP_OUT	AA8	0	OV _{DD}	2, 4
	Debug			
TRIG_IN	AB2	Ι	OV_{DD}	—
TRIG_OUT/READY/QUIESCE	AB1	0	OV _{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	0	OV_{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	0	OV_{DD}	6, 19, 29
MDVAL	AE5	0	OV_{DD}	6
CLK_OUT	AE21	0	OV _{DD}	11
	Clock			
RTC	AF16	Ι	OV_{DD}	—
SYSCLK	AH17	I	OV _{DD}	—

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{ ext{ heta}JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{ ext{ heta}JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{ ext{ heta}JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	R_{\thetaJB}	3	°C/W	3
Die junction-to-case	N/A	$R_{ ext{ heta}JC}$	0.8	°C/W	4

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Notes:

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
- 3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package Thermal	Characteristics for FC-PBGA
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Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{ extsf{ heta}JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{ extsf{ heta}JA}$	9	°C/W	1, 2

24 Document Revision History

The following table provides a revision history for this hardware specification.

Rev. Date Substantive Change(s) Number • Updated Section 21.2, "Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and 9 02/2012 Version 3.1.x Silicon with Stamped Lid," with version 3.0 silicon information. Added Figure 56, "Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA with Stamped Lid." • Updated Table 87, "Part Numbering Nomenclature," with version 3.0 silicon information. Removed Note from Section 5.1. "Power-On Ramp Rate". • Changed the Table 10 title to "Power Supply Ramp Rate". • Removed table 11. • Updated the title of Section 21.2, "Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid" to include Thermal Version 2.1.3 and Version 3.1.x Silicon. Corrected the leaded Solder Ball composition in Table 70, "Package Parameters" • Updated Table 87, "Part Numbering Nomenclature," with Version 3.1.x silicon information. • Updated the Min and Max value of TDO in the valid times row of Table 44, "JTAG AC Timing Specifications (Independent of SYSCLK)¹" from 4 and 25 to 2 and 10 respectively . 8 04/2011 Added Section 14.1, "GPOUT/GPIN Electrical Characteristics." • Updated Table 71, "MPC8548E Pinout Listing," Table 72, "MPC8547E Pinout Listing," Table 73, "MPC8545E Pinout Listing," and Table 74, "MPC8543E Pinout Listing," to reflect that the TDO signal is not driven during HRSET* assertion. • Updated Table 87, "Part Numbering Nomenclature" with Ver. 2.1.3 silicon information. In Table 37, "MII Management AC Timing Specifications, modified the fifth row from "MDC to MDIO 7 09/2010 delay tMDKHDX (16 x tptb_clk x 8) - 3 - (16 x tptb_clk x 8) + 3" to "MDC to MDIO delay tMDKHDX $(16 \times tCCB \times 8) - 3 - (16 \times tCCB \times 8) + 3."$ Updated Figure 55, "Mechanical Dimensions and Bottom Surface Nomenclature of the HiCTE FC-CBGA and FC-PBGA with Full Lid and figure notes. 6 12/2009 • In Section 5.1, "Power-On Ramp Rate" added explanation that Power-On Ramp Rate is required to avoid falsely triggering ESD circuitry. In Table 13 changed required ramp rate from 545 V/s for MVREF and VDD/XVDD/SVDD to 3500 V/s for MVREF and 4000 V/s for VDD. • In Table 13 deleted ramp rate requirement for XVDD/SVDD. In Table 13 footnote 1 changed voltage range of concern from 0-400 mV to 20-500mV. In Table 13 added footnote 2 explaining that VDD voltage ramp rate is intended to control ramp rate of AVDD pins. 5 10/2009 • In Table 27, "GMII Receive AC Timing Specifications," changed duty cycle specification from 40/60 to 35/75 for RX CLK duty cycle. Updated tMDKHDX in Table 37, "MII Management AC Timing Specifications." • Added a reference to Revision 2.1.2. • Updated Table 55, "MII Management AC Timing Specifications." Added Section 5.1, "Power-On Ramp Rate."

Table 88. Document Revision History